

BGB719L7ESD

SiGe:C Low Noise Amplifier MMIC for FM Radio Applications

Data Sheet

Revision 1.1, 2011-02-01
Preliminary

RF & Protection Devices

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Revision History

Page / Item	Subjects (major changes since last revisions)
Revision 1.1, 2011-02-01	
7	ESD values updated
12	AC Characteristics updated

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1 Features

Main features:

- High performance FM Radio LNA with integrated biasing
- Worldwide FM band support (76 MHz to 108 MHz)
- Low external parts count
- Super miniature low profile leadless package TSLP-7-8, 1.26 x 1.4 x 0.31 mm
- High gain at only 2.5 mA current consumption
- Integrated active biasing circuit enables stable operation point against temperature-, supply voltage- and processing-variations
- Integrated ESD protection for all pins (2 kV, HBM)
- High input compression point
- High input impedance
- Excellent noise figure from latest SiGe:C technology
- Operation voltage: 1.5 V to 4.0 V
- Power-off function
- Pb-free (RoHS compliant) and halogen-free (WEEE compliant) product



Applications

- Active matching for small FM radio antennas
- Portable headphone radio

Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions

Product Name	Package	Marking
BGB719L7ESD	TSLP-7-8	AW

2 Product Brief

The BGB719L7ESD is an advanced low noise amplifier MMIC with integrated ESD protection and active biasing specifically designed for FM antenna systems requiring high gain, reduced power consumption and low distortion. The device is based upon Infineon Technologies cost effective SiGe:C technology and comes in a low profile TSLP-7-8 leadless green package.

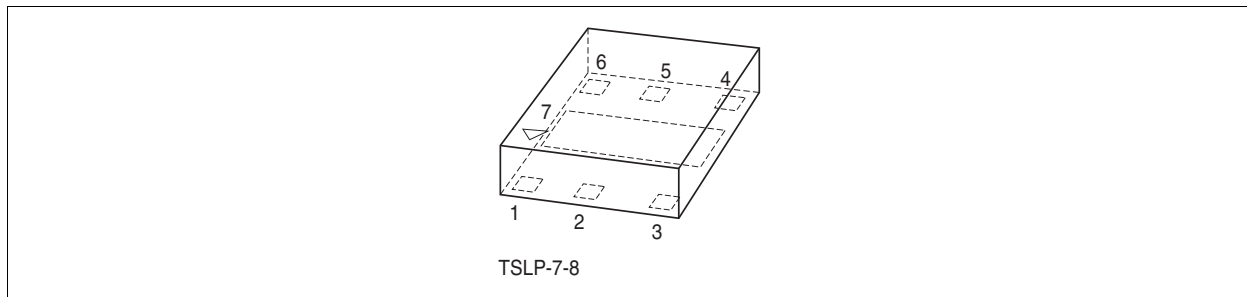


Figure 1 Pinning of BGB719L7ESD (top view)

Table 1 Pinning Table

Pin	Name	Function
1	V_{Ctrl}	On/Off control voltage
2	RF_{IN}	RF input
3	GND_{RF}	RF GND
4	NC	Not connected
5	RF_{OUT}	RF output
6	V_{CC}	Supply voltage
7	GND_{DC}	DC GND

The following function block in **Figure 2** shows the principal schematic how the BGB719L7ESD is used in a circuit. The Power On/Off function is controlled by applying V_{Ctrl} . Base- and collector voltages are applied internally.

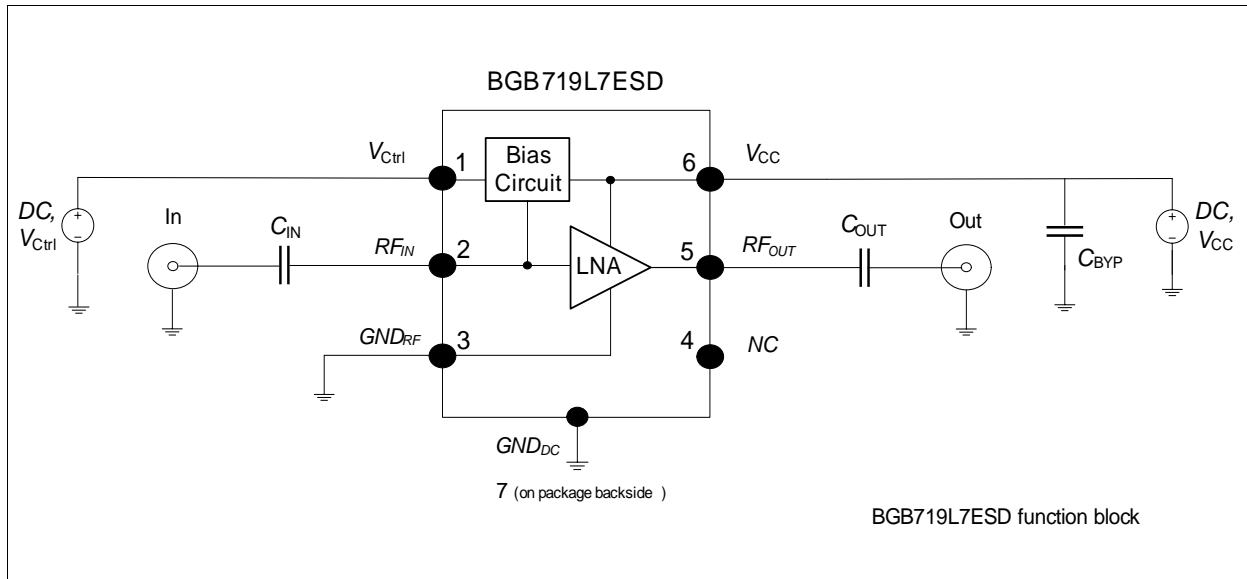


Figure 2 Function Block

The function of each component is explained in **Table 2**.

Table 2 Bill of Materials

Component	Value	Manufacturer / Type	Function
C_{IN}	330 pF	Various / 0402	DC blocking
C_{OUT}	330 pF	Various / 0402	DC blocking
C_{BYP}	47 nF	Various / 0402	Bypass capacitor

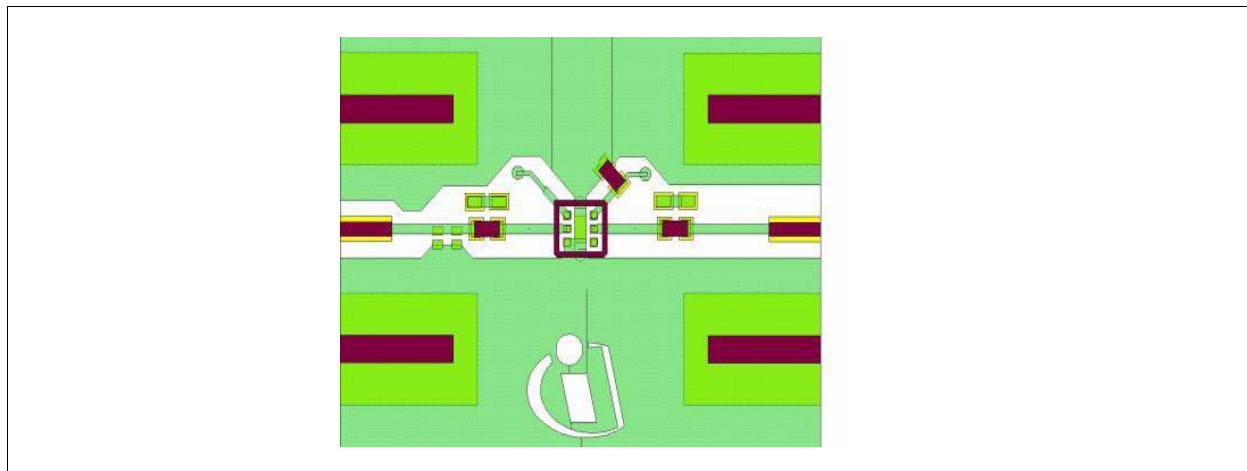


Figure 3 Application Board Drawing

3 Maximum Ratings

Table 3 Maximum Ratings at TA = 25°C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	V_{CC}	–	–	4.0	V	–
Supply current at V_{CC} pin	I_{CC}	–	–	25	mA	–
DC current at RF_{IN} Pin	I_B	–	–	3	mA	–
On/Off control voltage	V_{ctrl}	–	–	V_{CC}	V	–
Total power dissipation $T_S \leq 112\text{ °C}^1)$	P_{tot}	–	–	100	mW	–
Operation junction temperature	T_{JOp}	-55	–	150	°C	–
Storage temperature	T_{Stg}	-55	–	150	°C	–

1) T_S is the soldering point temperature. T_S is measured at the GND pin (7) at the soldering point to the pcb

Table 4 ESD Capability

Testing Model	Standard	Value	Unit
Human Body Model	JESD22-A114-B	2000	V
Machine Model	JESD22-A115-A	100	V
Charge Device Model	JESD22-C101-C	1500	V

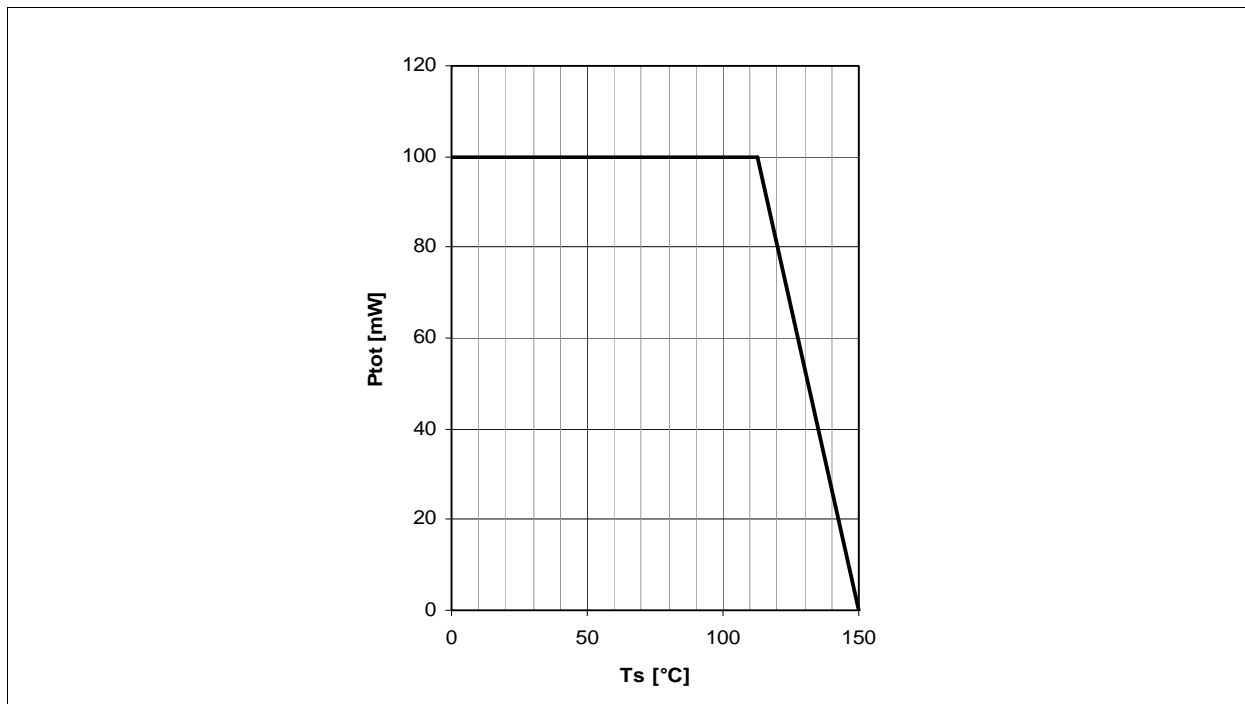
Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

4 Thermal Characteristics

Table 5 Thermal Resistance

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Junction - soldering point ¹⁾	R_{thJS}	–	375	–	K/W	

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance


Figure 4 Total Power Dissipation $P_{tot} = f(T_s)$

5 Operation Conditions

Table 6 Operation Conditions at $T_A = 25^\circ\text{C}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	V_{CC}	1.5	3.0	4.0	V	–
Voltage Ctrl On/Off pin in On mode	$V_{ctrl-on}$	1.2	3.0	V_{CC}	V	–
Voltage Ctrl On/Off pin in Off mode	$V_{ctrl-off}$	-0.3	0	0.3	V	–

6 Electrical Characteristics

6.1 DC Characteristics

Table 7 DC Characteristics at $T_A = 25\text{ °C}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply current	I_{CC}	2.0	2.5	3.2	mA	$V_{CC} = 3\text{ V}$ $V_{ctrl} = 3\text{ V}$ Small signal operation
Supply current in Off mode	I_{CC-off}	–	1	6	μA	$V_{CC} = 4.0\text{ V}$ $V_{ctrl} = 0\text{ V}$
Current into Ctrl On/Off pin in On mode	$I_{ctrl-on}$	–	14	20	μA	$V_{CC} = 3\text{ V}$ $V_{ctrl} = 3\text{ V}$
Current into Ctrl On/Off pin in Off mode	$I_{ctrl-off}$	–	–	0.1	μA	$V_{CC} = 4.0\text{ V}$ $V_{ctrl} = 0\text{ V}$

6.2 AC Characteristics

Table 8 AC characteristics¹⁾: $T_A = 25\text{ °C}$, $V_{CC} = 3\text{ V}$, $V_{ctrl} = 3\text{ V}$, $f = 100\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Insertion power gain	$ S_{21} $		13		dB	–
Input return loss ²⁾	RL_{IN}	–	0.5 ³⁾	–	dB	–
Output return loss ²⁾	RL_{OUT}	–	11	–	dB	–
Noise figure ⁴⁾	$F_{50\Omega}$	–	1.2	–	dB	$Z_s = 50\ \Omega$
Input 1dB gain compression point ²⁾	IP_{-1dB}	–	-6	–	dBm	–
Input 3rd Order Intercept Point ²⁾	IIP_3	–	-14.5	–	dBm	$P_{RFIN} = -40\text{ dBm}$

1) Measured on BGB719L7ESD application board according to application schematic on [Figure 2](#), including PCB losses (unless noted otherwise)

2) Verified by random sampling

3) High LNA input impedance leads to power matching with high ohmic antennas

4) An aggressive low pass filter prevents radio broadcast signals from distorting the NF measurement

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